

TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE

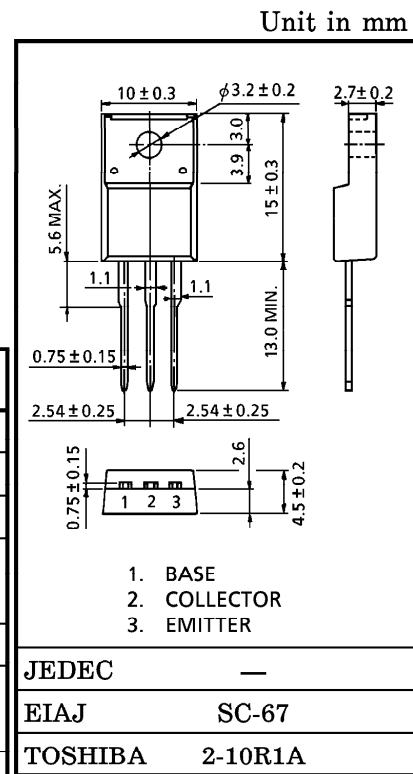
2SB1481

SWITCHING APPLICATIONS

- High DC Current Gain
: $h_{FE} = 2000$ (Min.) ($V_{CE} = -2V$, $I_C = -1.5A$)
- Low Saturation Voltage : $V_{CE(sat)} = -1.5V$ (Max.) ($I_C = -3A$)
- Complementary to 2SD2241

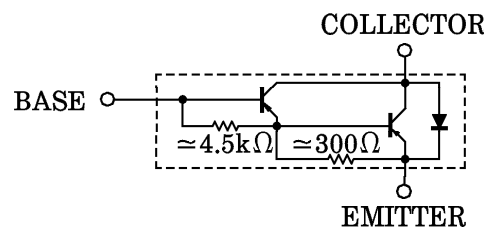
MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-100	V
Collector-Emitter Voltage	V_{CEO}	-100	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	DC	I_C	± 4
	Pulse	I_{CP}	± 6
Base Current	I_B	-0.3	A
Collector Power Dissipation	$T_a = 25^\circ C$	P_C	2.0
	$T_c = 25^\circ C$		25
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55~150	$^\circ C$



Weight : 1.7g

EQUIVALENT CIRCUIT



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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	$V_{CB} = -100V, I_E = 0$	—	—	-2.0	μA
Emitter Cut-off Current		I_{EBO}	$V_{EB} = -5V, I_C = 0$	—	—	-2.5	mA
Collector-Emitter Breakdown Voltage		$V_{(BR) CEO}$	$I_C = -10mA, I_B = 0$	-100	—	—	V
DC Current Gain	$h_{FE} (1)$		$V_{CE} = -2V, I_C = -1.5A$	2000	—	—	
	$h_{FE} (2)$		$V_{CE} = -2V, I_C = -3A$	1000	—	—	
Collector-Emitter Saturation Voltage		$V_{CE (sat)}$	$I_C = -3A, I_B = -6mA$	—	—	-1.5	V
Base-Emitter Saturation Voltage		$V_{BE (sat)}$	$I_C = -3A, I_B = -6mA$	—	—	-2.0	V
Collector-Emitter Reverse Voltage		V_{ECO}	$I_C = 1A, I_B = 0$	—	—	2.0	V
Switching Time	Turn-on Time	t_{on}	<p> $-I_{B1} = I_{B2} = 6mA$ $V_{CC} = -30V$ $DUTY\ CYCLE \leq 1\%$ </p>	—	0.15	—	μs
	Storage Time	t_{stg}		—	0.80	—	
	Fall Time	t_f		—	0.40	—	

